

Sonic Fast Recovery Diode

$$V_{RRM} = 1800 \text{ V}$$

$$I_{FAV} = 10 \text{ A}$$

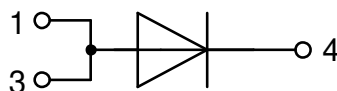
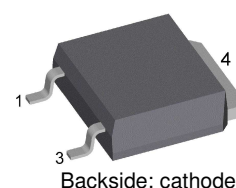
$$t_{rr} = 260 \text{ ns}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

Part number

DHG10IM1800UZ

Marking on Product: HAVGZI



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

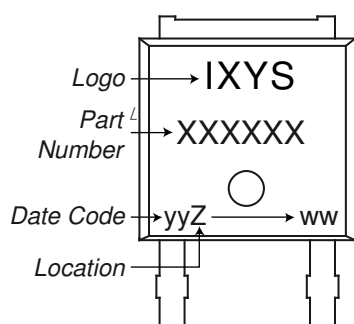
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
I_R	reverse current, drain current	$V_R = 1800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			50	μA
		$V_R = 1800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0.4	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.27	V
		$I_F = 20\text{ A}$				2.94	V
		$I_F = 10\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			2.43	V
		$I_F = 20\text{ A}$				3.42	V
I_{FAV}	average forward current	$T_C = 110^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			10	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		1.40	V
r_F	slope resistance					101	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				85	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			60	A
C_J	junction capacitance	$V_R = 200\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		3		pF
I_{RM}	max. reverse recovery current	$I_F = 10\text{ A}; V_R = 900\text{ V}$ $-di_F/dt = 350\text{ A}/\mu\text{s}$		$T_{VJ} = 25^{\circ}\text{C}$		15	A
				$T_{VJ} = 150^{\circ}\text{C}$		17.5	A
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		260	ns
				$T_{VJ} = 150^{\circ}\text{C}$		350	ns

Package TO-252 (DPak)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				20	A
T_{VJ}	virtual junction temperature			-55		175	°C
T_{op}	operation temperature			-55		150	°C
T_{stg}	storage temperature			-55		150	°C
Weight					0.3		g
F_c	mounting force with clip			20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal		3.6			mm
$d_{Spb/Apb}$		terminal to backside		3.0			mm

Product Marking



Part description

D = Diode
 H = Sonic Fast Recovery Diode
 G = extreme fast
 10 = Current Rating [A]
 IM = Single Diode
 1800 = Reverse Voltage [V]
 UZ = TO-252AA (DPak) (2HV)

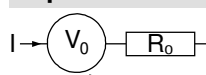
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10IM1800UZ-TRL	HAVGZI	Tape & Reel	2500	526360
Alternative	DHG10IM1800UZ-TUB	HAVGZI	Tube	70	526353

Similar Part	Package	Voltage class
DHG10I1800PA	TO-220AC (2)	1800

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Fast Diode

$V_{0\max}$ threshold voltage

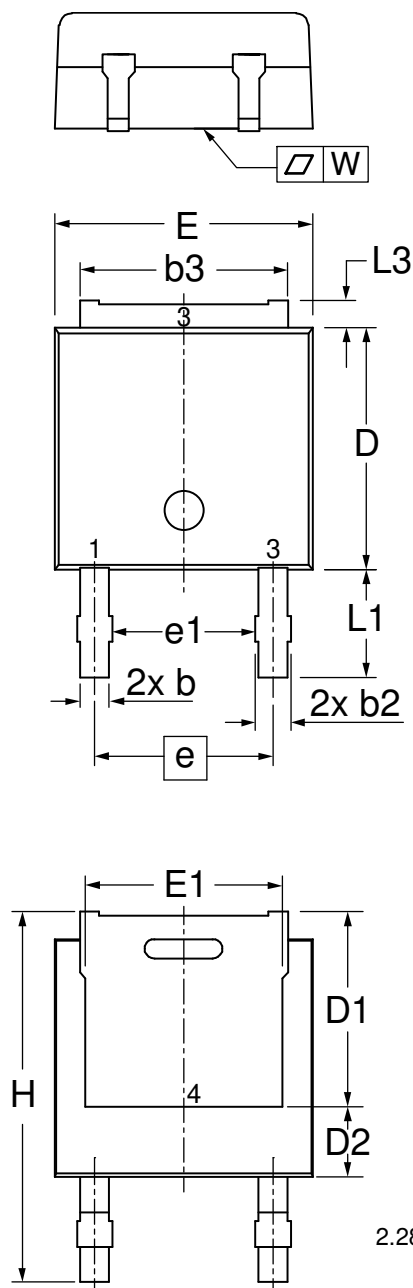
1.4

V

$R_{0\max}$ slope resistance *

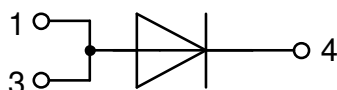
98

mΩ

Outlines TO-252 (DPak)


Dim	Millimeters		Inches	
	min	max	min	max
A	2.18	2.39	0.086	0.094
A1	0.00	0.13	0.000	0.005
A2	0.97	1.17	0.038	0.046
b	0.64	0.89	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	5.08	5.59	0.200	0.220
c	0.46	0.61	0.018	0.024
c2	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.57	5.21	0.180	0.205
D2	2.03		0.080	
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	4.57		0.180	
e1	3.62		0.143	
H	9.15	10.34	0.360	0.407
L	1.40	1.78	0.055	0.070
L1	2.54	2.92	0.100	0.115
L3	0.64	1.02	0.025	0.040
W	typ. 0.02	0.040	typ. 0.0008	0.000

Recommended min. foot print



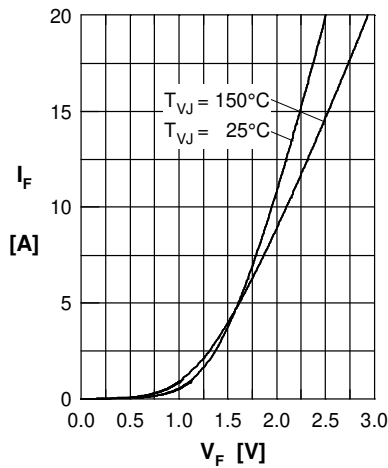
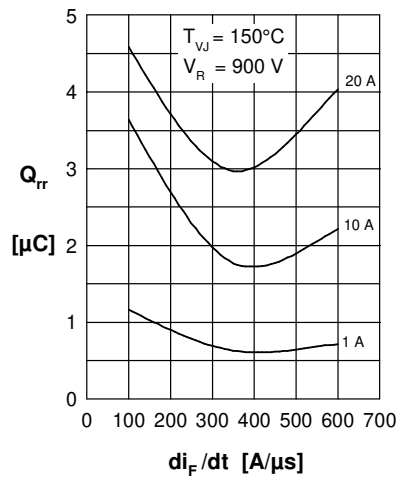
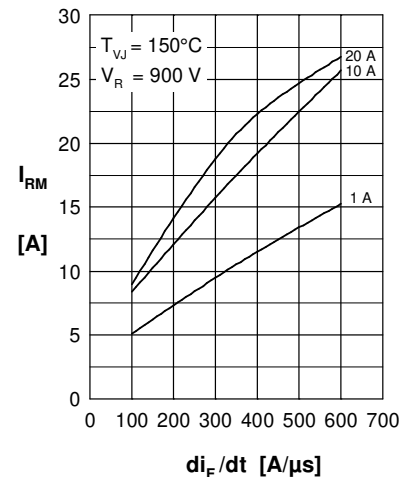
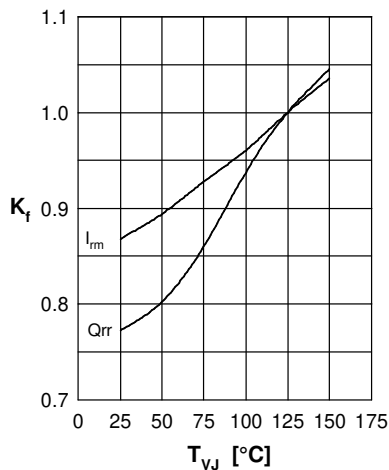
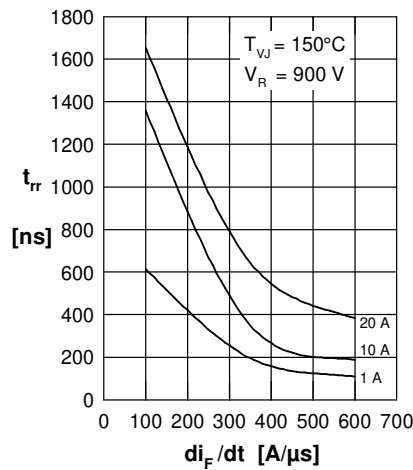
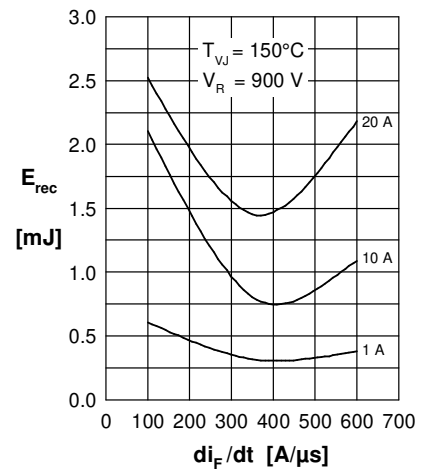
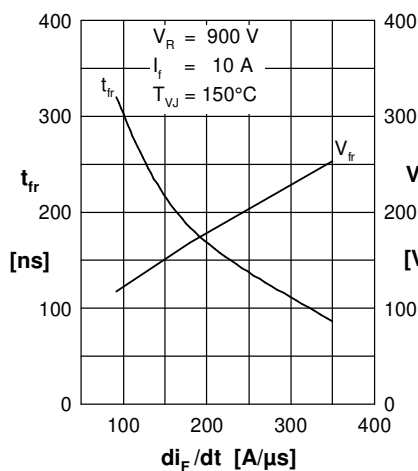
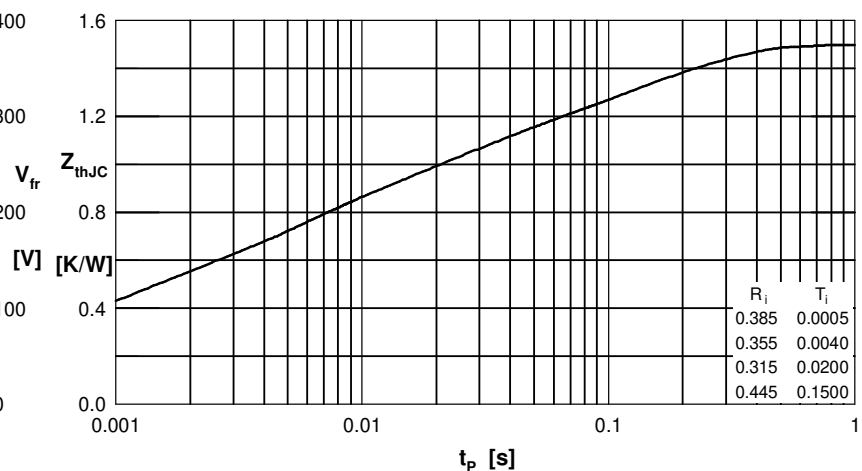
Fast Diode

 Fig. 1 Typ. Forward current versus V_F

 Fig. 2 Typ. reverse recov. charge Q_{rr} versus di_F/dt

 Fig. 3 Typ. peak reverse current I_{RM} versus di_F/dt

 Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

 Fig. 6 Typ. recovery energy E_{rec} versus di_F/dt

 Fig. 7 Typ. peak forward voltage V_{fr} and t_{fr} versus di_F/dt


Fig. 8 Typ. transient thermal impedance junction to case